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a three dimensional marker indicating the location of the light emitting region,  
wherein the three dimensional marker is located in the indicator region.

✓ 2. (Twice Amended) The semiconductor laser as claimed in claim 1, wherein the  
three-dimensional marker is at least one of a concavity and a convexity formed on the  
laser beam-emitting facet in the indicator region.

✓ 3. (Amended) The semiconductor laser as claimed in claim 1, further comprising  
a light-shielding film covering at least the light-emitting region, the light shielding film  
having a small opening in part of the portion of the light shielding film covering the  
light-emitting region.

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✓ 5. (Amended) The semiconductor laser as claimed in claim 3, wherein the light-  
shielding film further covers the three-dimensional marker.

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✓ 6. (Twice Amended) The semiconductor laser as claimed in claim 3, further  
comprising a dielectric film provided between the laser beam-emitting facet and the light-  
shielding film, wherein part of the dielectric film is exposed at the small opening.

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✓ 8. (Twice Amended) A method of producing a semiconductor laser having a  
laser beam-emitting facet including a light-emitting region, the method comprising:  
forming an indicator region at a location on the laser beam-emitting facet that has a  
prescribed positional relationship with the light-emitting region, the indicator region  
having a three dimensional marker located thereon.

b2 9. (Amended) The method as claimed in claim 8, further comprising forming a light-shielding film covering at least the light-emitting region, and forming the light-shielding film within a small opening at a location having a prescribed positional relationship with the three-dimensional marker .

✓ 10. (Amended) The method as claimed in claim 9, wherein the forming of the indicator region and the forming of the small opening both utilize focused ion beam processing.

b2 11. (Twice Amended) The method as claimed in claim 8, further comprising irradiating at least the light-emitting region of the laser beam-emitting facet with a focused ion beam before forming of the indicator region .

✓ 12. (Twice Amended) The method as claimed in claim 9, further comprising irradiating at least the light emitting region of the laser beam-emitting facet with a focused ion beam before the forming of the indicator region .

b7 14. (Twice Amended) An evanescent optical head system comprising:  
an evanescent optical head for reading/writing of data from/to a recording medium using evanescent light; and  
a semiconductor laser coupled to the evanescent optical head for emitting the evanescent light, the laser having a laser beam-emitting facet including a light-emitting region, the laser comprising:  
an indicator region formed on the laser beam-emitting facet;

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a light shielding film covering at least the light-emitting region; and  
a small opening for emitting the evanescent light formed in the light-shielding film at a  
location that has a prescribed positional relationship with the indicator region.

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Please add new claims 15-20 as follows:

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15. (Newly Added) The evanescent optical head as claimed in claim 14, further  
comprising a three-dimensional marker located in the indicator region.

/16. (Newly Added) A semiconductor laser assembly including a semiconductor  
laser having a laser beam-emitting facet comprising:  
a light-emitting region formed on the laser beam-emitting facet;  
an indicator region formed at a region different from the light-emitting region;  
and  
a three dimensional marker indicating the location of the light emitting region,  
wherein the three dimensional marker is located in the indicator region.

/17. (Newly Added) The semiconductor laser assembly as claimed in claim 16,  
wherein the three-dimensional marker is at least one of a concavity and a convexity  
formed on the laser beam-emitting facet in the indicator region.

/18. (Newly Added) The semiconductor laser assembly as claimed in claim 16,  
further comprising a light-shielding film covering at least the light-emitting region, the  
light shielding film being formed with a small opening at part of the portion of the light  
shielding film covering the light-emitting region.

B3 19. (Newly Added) The semiconductor laser assembly as claimed in claim 18,  
wherein the light-shielding film further covers the three-dimensional marker.

20. (Newly Added) The semiconductor laser assembly as claimed in claim 18,  
further comprising a dielectric film provided between the laser beam-emitting facet and  
the light-shielding film, part of the dielectric film being exposed at the small opening.

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PLEASE SEE THE ATTACHED PAGES SHOWING THE AMENDMENTS IN FULL.

1. (Twice Amended) A semiconductor laser having a laser beam-emitting facet ~~including a laser beam-emitting region~~, the semiconductor laser comprising:  
a light-emitting region formed on the laser beam-emitting facet;  
an indicator region spaced at a distance -a three dimensional feature portion  
indicating the location of the light-emitting region formed on the laser beam-emitting  
facet ~~a region different from the light-emitting region~~; and  
a three dimensional marker indicating the location of the light emitting region,  
wherein the three dimensional marker is located in the indicator region.
2. (Twice Amended) The semiconductor laser as claimed in claim 1, wherein the  
three-dimensional marker feature portion is at least one of a concavity and a convexity  
formed on the laser beam-emitting facet in the indicator region ~~at a region different from~~  
~~the light-emitting region.~~
3. (Amended) The semiconductor laser as claimed in claim 1, further comprising  
a light-shielding film covering at least the light-emitting region, the light shielding film  
having being formed with a small opening at in part of the portion of the light shielding  
film covering over the light-emitting region.
5. (Amended) The semiconductor laser as claimed in claim 3, wherein the light-  
shielding film further covers the three-dimensional marker feature portion.

6. (Twice Amended) The semiconductor laser as claimed in claim 3, further comprising a dielectric film provided between the laser beam-emitting facet and the light-shielding film, wherein part of the dielectric film is being exposed at the small opening.

8. (Twice Amended) A method of producing a semiconductor laser having a laser beam-emitting facet including a light laser beam-emitting region, the method comprising: a step of forming an three-dimensional indicator feature portion region at a location on the laser beam-emitting facet that has to have a prescribed positional relationship with the light-emitting region, the indicator region having a three dimensional marker located thereon.

9. (Amended) The method as claimed in claim 8, further comprising a step of forming a light-shielding film covering at least the light-emitting region, and a step of forming the light-shielding film within a small opening at a location having a prescribed positional relationship with the three-dimensional marker feature portion.

10. (Amended) The method as claimed in claim 9, wherein the step of forming of the indicator region three-dimensional feature portion and the step of forming of the small opening both utilize focused ion beam processing.

11. (Twice Amended) The method as claimed in claim 8, further comprising a step of irradiating at least the light-emitting region of the laser beam-emitting facet with a focused ion beam before the step of forming of the indicator region three-dimensional feature portion.

12. (Twice Amended) The method as claimed in claim 9, further comprising a ~~step of~~ irradiating at least the light emitting region of the laser beam-emitting facet with a focused ion beam before the ~~step of~~ forming of the indicator region three-dimensional feature portion.

14. (Twice Amended) An evanescent optical head system comprising:

~~A~~an evanescent optical head for reading/writing of data from/to a recording medium using evanescent light; ~~and; the evanescent optical head being equipped with~~  
a semiconductor laser coupled to the evanescent optical head for emitting the evanescent light, the laser having ~~that has~~ a laser beam-emitting facet including a light-emitting region, the laser comprisesing:

an indicator region three-dimensional feature portion formed on the laser beam-emitting facet;

a light shielding film covering at least the light-emitting region; and

a small opening for emitting the evanescent light formed in the light-shielding film at a location that has ~~to have~~ a prescribed positional relationship with the indicator region three-dimensional feature portion.